

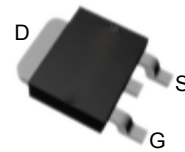
Features

- 100V/115A
 $R_{DS(ON)}=4.5m\Omega(typ.)@V_{GS}=10V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

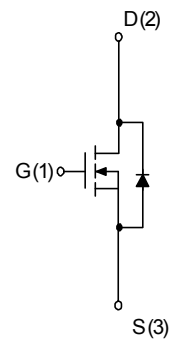
Applications

- Power Management for SMPS.
- DC/DC Converter.

Pin Description



Top View of TO-252-2



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	115	A
I _D	Continuous Drain Current	T _C =25°C	115	A
		T _C =100°C	46	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	345	
P _D	Maximum Power Dissipation	T _C =25°C	125	W
		T _C =100°C	50	
R _{θJC}	Thermal Resistance-Junction to Case		1	°C/W
I _D	Continuous Drain Current	T _A =25°C	12.3	A
		T _A =70°C	9.8	
P _D	Maximum Power Dissipation	T _A =25°C	2.5	W
		T _A =70°C	1.6	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient		50	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	36	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	324	mJ

Note * : Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 80A.

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Note c : Surface Mounted on 1in^2 pad area.

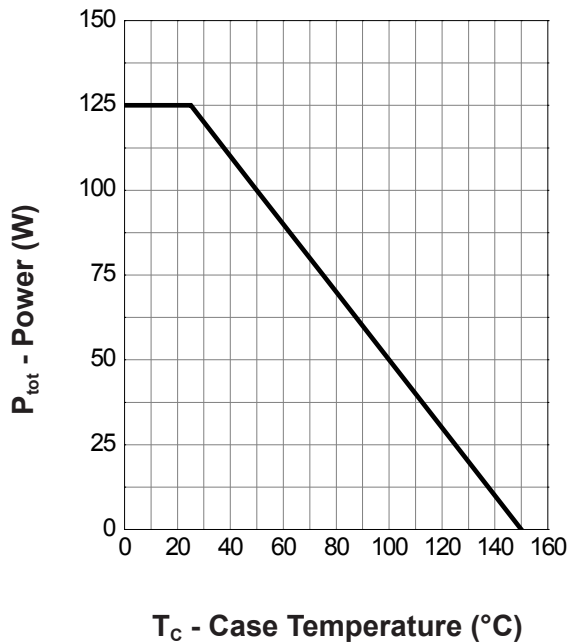
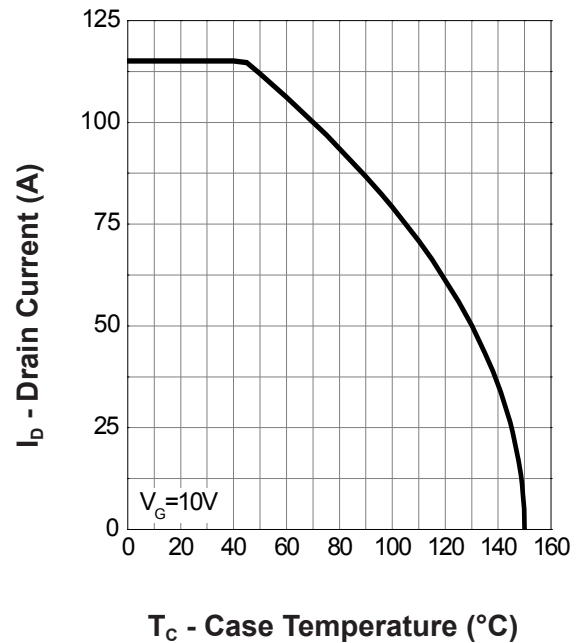
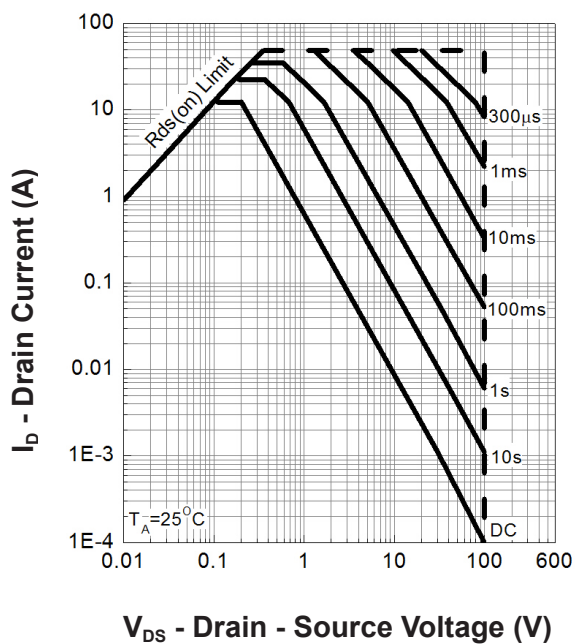
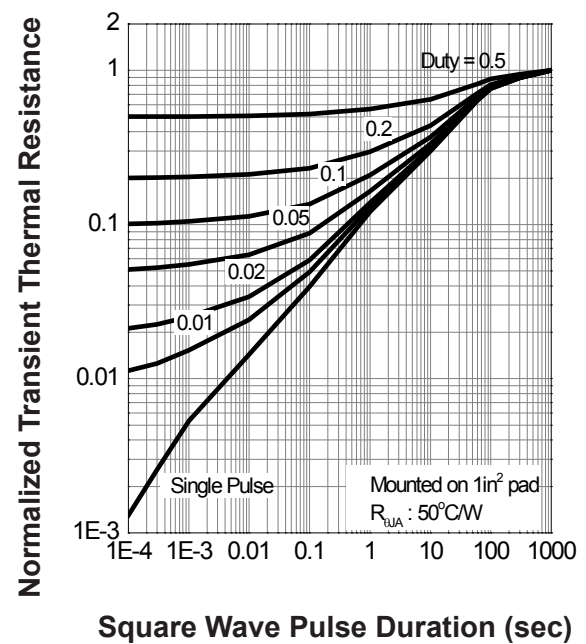
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =27A	-	4.5	5.5	mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =15A, V _{GS} =0V	-	0.8	1.3	V
t _{rr} ^e	Reverse Recovery Time	I _{SD} =27A, dI _{SD} /dt=100A/μs	-	50	-	ns
Q _{rr} ^e	Reverse Recovery Charge		-	106	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, Frequency=1.0MHz	-	4950	-	pF
C _{oss}	Output Capacitance		-	1405	-	
C _{rss}	Reverse Transfer Capacitance		-	200	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	22	40	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	48	87	
t _f	Turn-off Fall Time		-	77	139	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =27A	-	42	60	nC
Q _{gs}	Gate-Source Charge		-	13.5	-	
Q _{gd}	Gate-Drain Charge		-	9	-	

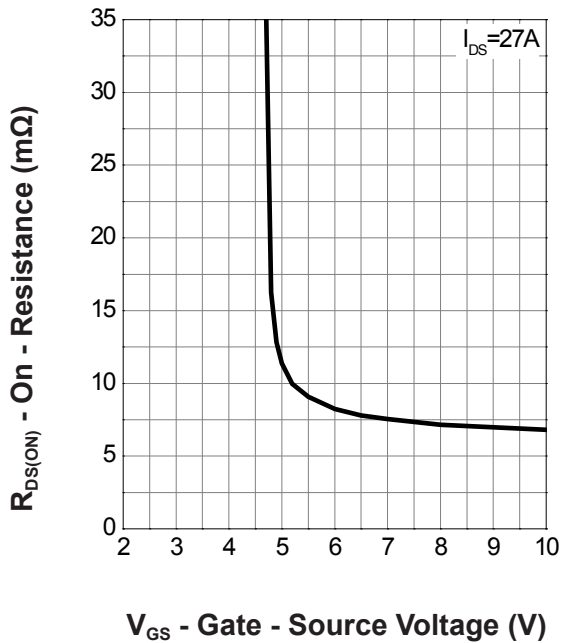
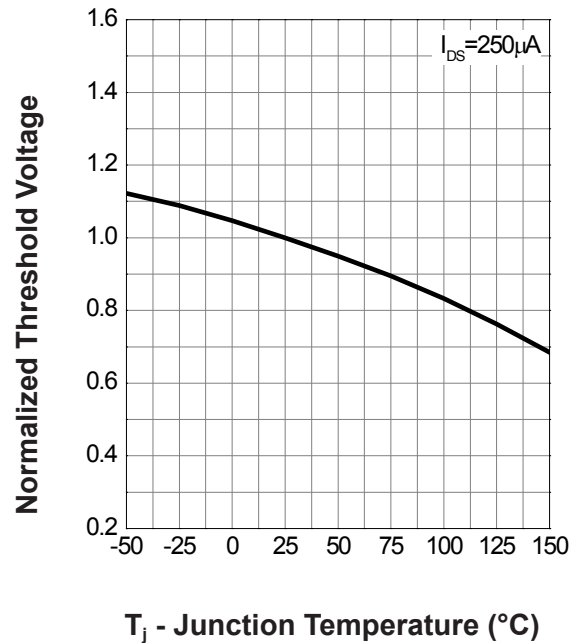
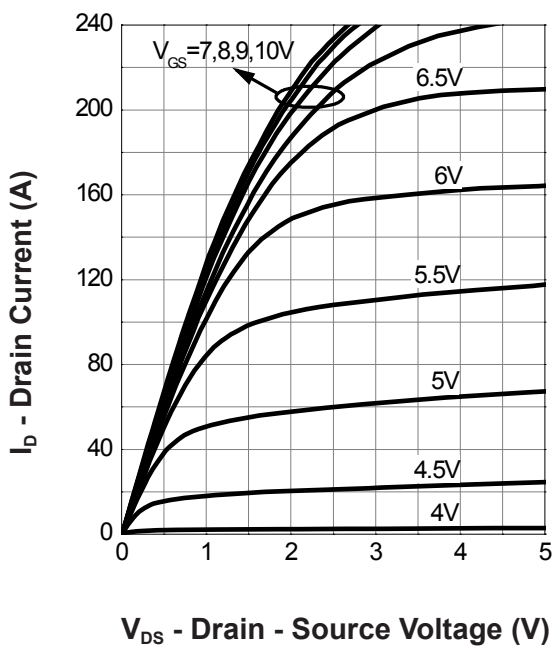
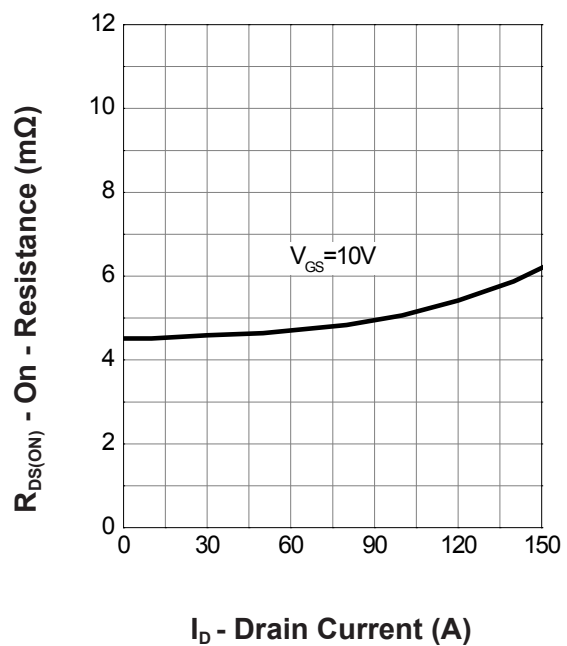
Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

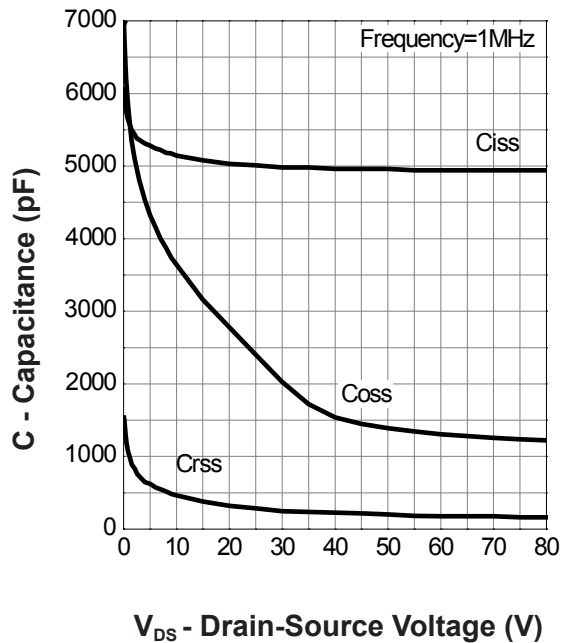
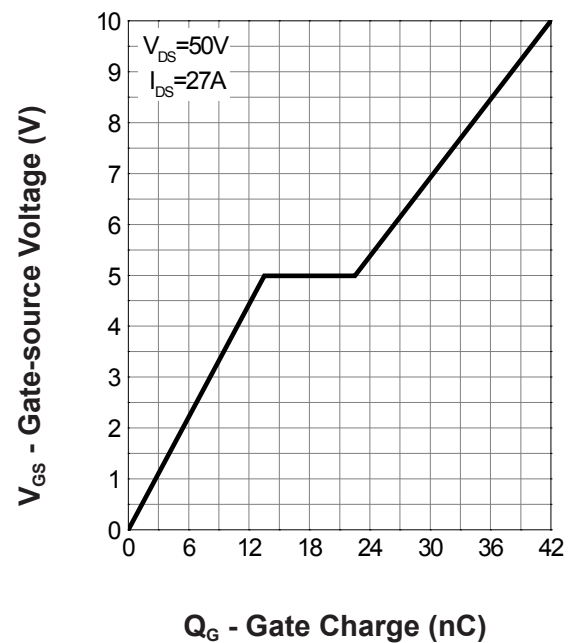
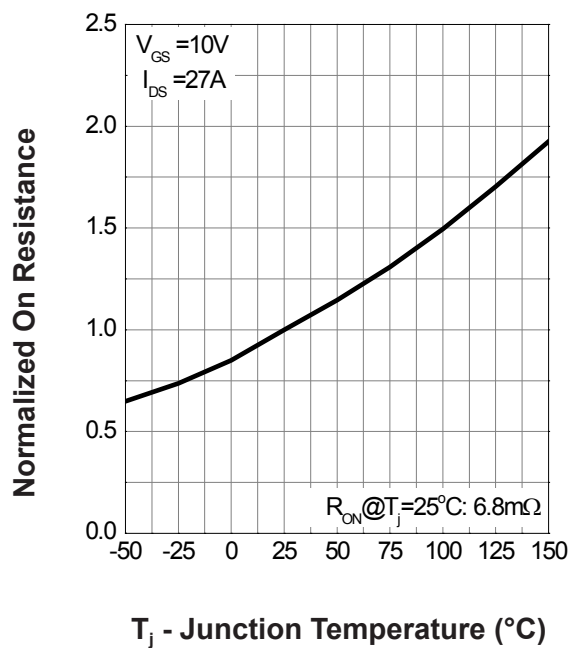
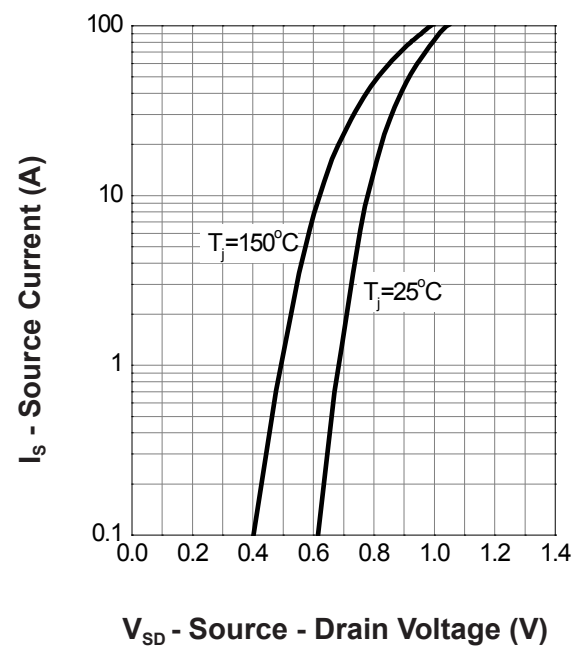
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


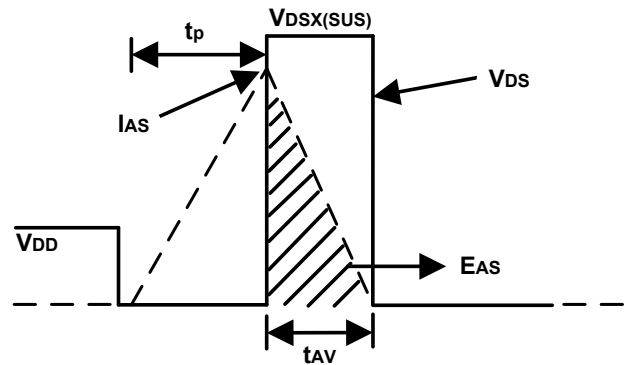
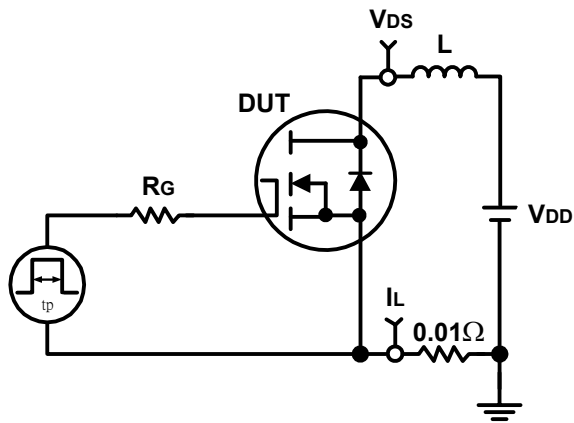
Typical Operating Characteristics(Cont.)

Gate-Source On Resistance

Gate Threshold Voltage

Output Characteristics

Drain-Source On Resistance


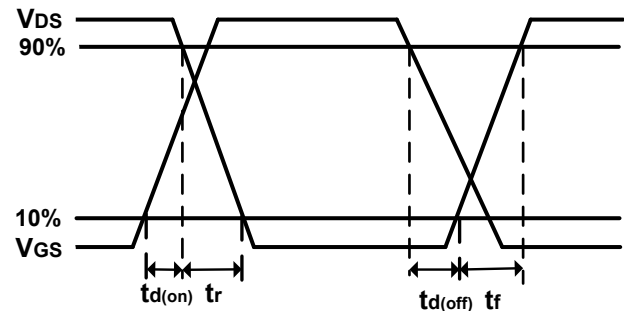
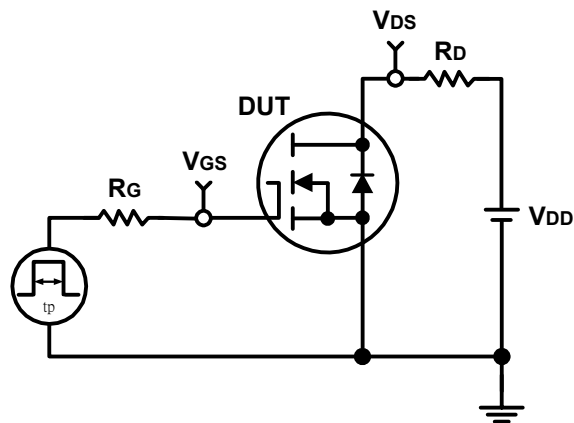
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

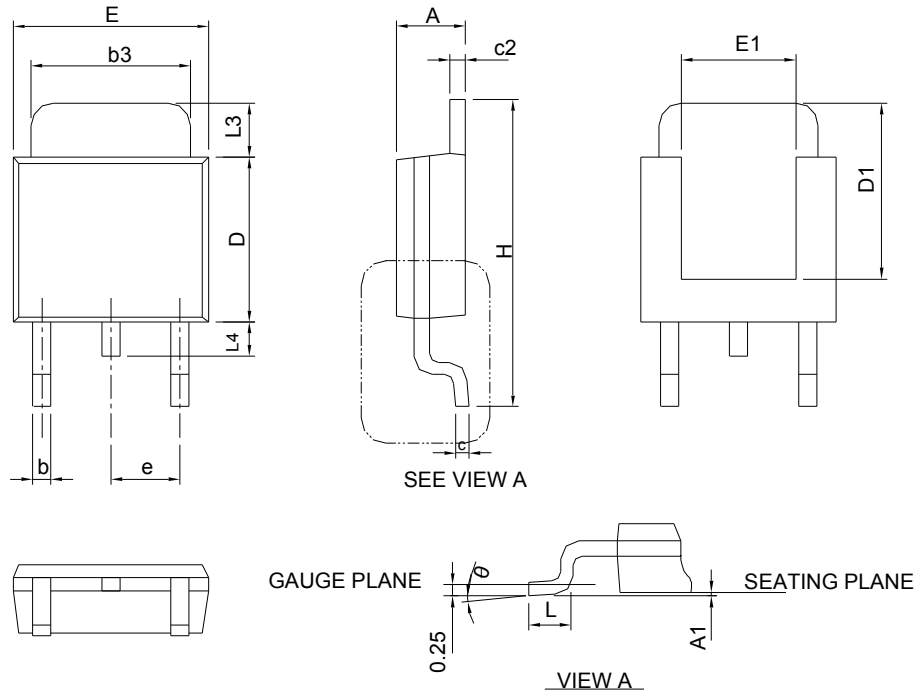


Switching Time Test Circuit and Waveforms



Package Information

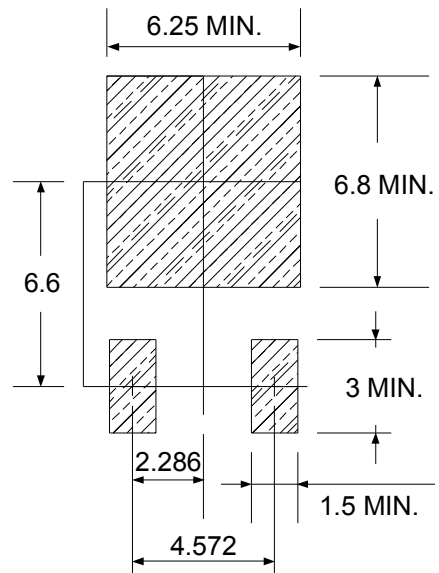
TO-252-2



SYMBOL	TO-252-2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

RECOMMENDED LAND PATTERN



UNIT: mm